

EXPRESS MAIL NO. EV035490605US Attorney Docket No. FUJ 00-01013RAM Client/Matter No. 80458.0007

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Glen Fox, Fan Chu, Brian Eastep, Tomohiro Takamatsu, Ko Nakamura, and Yoshimasa Horii

:-IN- 00/740 204

Serial No. 09/742,204

Filed: December 20, 2000

For: PROCESS FOR PRODUCING HIGH QUALITY PZT FILMS FOR FERROELECTRIC MEMORY INTEGRATED

CIRCUITS

Group Art Unit: 2811

Examiner:

CERTIFICATE OF MAILING BY EXPRESS MAIL

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

The undersigned hereby certifies that the following documents:

1. Preliminary Amendment;

2. Certificate of Mailing by Express Mail; and

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3. Return Postcard

relating to the above application, were deposited as "Express Mail", Mailing Label No. EV035490605US with the United States Postal Service, addressed to The Assistant Commissioner for Patents, Washington, D.C., 20231, on & December 2001

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Peter J. Meza, Reg. No. 32,920

HOGAN & HARTSON TEP

One Tabor Center

1200 17th Street, Suite 1500

Denver, Colorado 80202

(719) 448-5906 Tel

(303) 899-7333 Fax



Atty. Docket No. FUJ 00-01013RAM Client Matter No. 80458.0007 Express Mail Label No. EV035490605US

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PRELIMINARY AMENDMENT

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Please amend the above-identified patent application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 7, line 1, with the following:

Figure 3 is a process flowchart illustrating an alternative process wherein the top electrode layer is deposited following a first RTA anneal, and a second RTA anneal is performed after etching of the PZT;

Please replace the paragraph beginning at page 7, line 5, with the following:

Figure 4 is a process flowchart illustrating an alternative process wherein the top electrode layer is deposited following a first RTA anneal, and a second RTA anneal is performed after etching of the PZT and deposition of an encapsulation layer; and

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